Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application

Listing of Claims:

1. (Original) A substrate for a semiconductor light-emitting element comprises, on a set base material, a group III nitride underlayer which contains at least Al, said group III nitride underlayer having a dislocation density of $\leq 1 \times 10^{11}/cm^2$ and a (002) plane X-ray rocking curve half-width value of ≤ 200 seconds, a p-type semiconductor layer group is formed above said group III nitride underlayer and comprises a group III nitride having a Ga content relative to the total group III elements of $\geq 50\%$ and a carrier density of $\geq 1 \times 10^{16}/cm^3$, a light-emitting layer is formed on said p-type semiconductor layer and has the form of insular crystals comprising a group III nitride and produces quantum effects, and an n-type semiconductor layer group is formed on said light-emitting layer and has a Ga content relative to the total group III elements of $\geq 50\%$.

2. (Original) The substrate for a semiconductor light-emitting element as claimed in Claim 1, wherein the Al content in said group III nitride underlayer relative to the total group III elements present in said group III nitride underlayer is $\geq 50\%$.

3. (Original) The substrate for a semiconductor light-emitting element as claimed in Claim 2, wherein said group III nitride underlayer comprises AlN.

4. (Original) The substrate for a semiconductor light-emitting element as claimed in claim 1, wherein said group III nitride underlayer is formed by a CVD procedure at a temperature of ≥1100°C.

5. (Original) The substrate for a semiconductor light-emitting element as claimed in claim 1, wherein said light-emitting layer having said insular crystals includes rare earth metal or transition metal atoms.

6. (Original) The substrate for a semiconductor light-emitting element as claimed in claim 1, wherein said light-emitting layer having said insular crystals consists of plural layers.

7. (Original) The substrate for a semiconductor light-emitting element as claimed in claim 1, wherein said carrier density of said p-type semiconductor layer group is $\geq 1\times10^{17}/cm^3$.

8. (Original) A semiconductor light-emitting element comprises, on a set base material, a group III nitride underlayer formed on said base material including at least Al, a dislocation density of $\leq 1 \times 10^{11}/cm^2$ and a (002) plane X-ray rocking curve half-width value of ≤200 seconds, a p-type semiconductor layer group is formed above said group III nitride underlayer and comprises a group III nitride having a Ga content relative to the total group III elements of ≥50% and a carrier density of $\geq 1 \times 10^{16}/cm^3$, a light-emitting layer is formed on said p-type semiconductor layer and has the form of insular crystals comprising a group III nitride and produces quantum effects, and an n-type semiconductor layer group is formed on said light-emitting layer and has a Ga content relative to the total group III elements of ≥50%.

9. (Original) The semiconductor light-emitting element as claimed in Claim 8, wherein the Al content in said group III nitride underlayer relative to the total group III elements present in said group III nitride underlayer is $\geq 50\%$.

10. (Original) The semiconductor light-emitting element as claimed in Claim 9, wherein said group III nitride underlayer comprises AlN.

11. (Original) The semiconductor light-emitting element as claimed in claim 8, wherein said light-emitting layer having said insular crystals includes rare earth metal or transition metal atoms.

12. (Original) The semiconductor light-emitting element as claimed in claim 8, wherein said light-emitting layer having said insular crystals consists of plural layers.

13. (Original) The semiconductor light-emitting element as claimed in claim 8, wherein said carrier density of said p-type semiconductor layer group is $\geq 1 \times 10^{17}/cm^3$.

Claims 14-17 (Cancelled)